



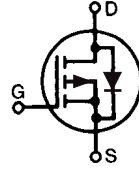
**THE DATASHEET OF  
IXTH52P10P**



## PolarP™ Power MOSFET

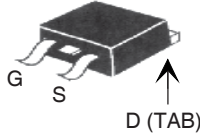
P-Channel Enhancement Mode  
Avalanche Rated

**IXTA52P10P**  
**IXTH52P10P**  
**IXTP52P10P**  
**IXTQ52P10P**

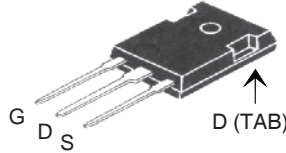


$V_{DSS} = -100V$   
 $I_{D25} = -52A$   
 $R_{DS(on)} \leq 50m\Omega$

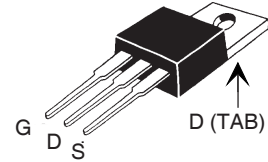
TO-263 (IXTA)



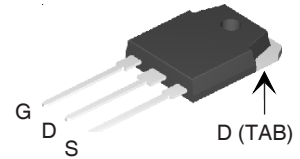
TO-247 (IXTH)



TO-220 (IXTP)



TO-3P (IXTQ)



G = Gate      D = Drain  
S = Source    TAB = Drain

Symbol	Test Conditions	Maximum Ratings	
		Value	Unit
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	-100	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	-100	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$	- 52	A
$I_{DM}$	$T_C = 25^\circ C$ , pulse width limited by $T_{JM}$	-130	A
$I_{AR}$	$T_C = 25^\circ C$	- 52	A
$E_{AS}$	$T_C = 25^\circ C$	1.5	J
<b>dV/dt</b>	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	10	V/ns
$P_D$	$T_C = 25^\circ C$	300	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	1.6mm (0.062 in.) from case for 10s	300	$^\circ C$
$T_{SOLD}$	Plastic body for 10s	260	$^\circ C$
$M_d$	Mounting torque (TO-3P, TO-220, TO-247)	1.13/10	Nm/lb.in.
<b>Weight</b>	TO-247	6.0	g
	TO-3P	5.5	g
	TO-220	3.0	g
	TO-263	2.5	g

### Features:

- International standard packages
- Fast intrinsic diode
- Dynamic dV/dt Rated
- Avalanche Rated
- Rugged PolarP™ process
- Low  $Q_G$  and  $R_{ds(on)}$  characterization
- Low Drain-to-Tab capacitance
- Low package inductance
- easy to drive and to protect

### Applications:

- High side switching
- Push-pull amplifiers
- DC Choppers
- Current regulators
- Automatic test equipment

### Advantages:

- Low gate charge results in simple drive requirement
- Improved Gate, Avalanche and dynamic dV/dt ruggedness
- High power density
- Fast switching
- Easy to parallel

Symbol	Test Conditions ( $T_J = 25^\circ C$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = -250\mu A$	-100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	- 2.5		V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$			-10 $\mu A$
	$V_{GS} = 0V$ $T_J = 125^\circ C$			-150 $\mu A$
$R_{DS(on)}$	$V_{GS} = -10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			50 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = -10\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1	12	20	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = -25\text{V}$ , $f = 1\text{MHz}$		2845	pF
$C_{oss}$			1015	pF
$C_{rss}$			275	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = -10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 3.3\Omega$ (External)		22	ns
$t_r$			29	ns
$t_{d(off)}$			38	ns
$t_f$			22	ns
$Q_{g(on)}$	$V_{GS} = -10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$		60	nC
$Q_{gs}$			17	nC
$Q_{gd}$			23	nC
$R_{thJC}$			0.42	$^\circ\text{C/W}$
$R_{thCS}$	(TO-3P)(TO-247)		0.21	$^\circ\text{C/W}$
	(TO-220)		0.50	$^\circ\text{C/W}$

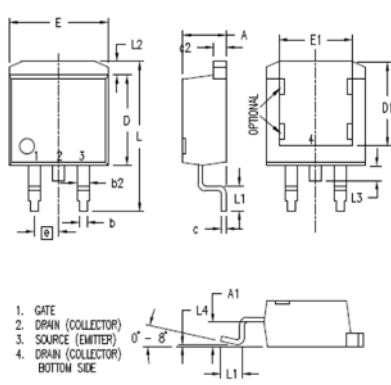
**Source-Drain Diode**

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			- 52 A
$I_{SM}$	Repetitive, pulse width limited by $T_{JM}$			- 200 A
$V_{SD}$	$I_F = -26\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1			- 3.5 V
$t_{rr}$	$I_F = -26\text{A}$ , $-di/dt = -100\text{A}/\mu\text{s}$ $V_R = -50\text{V}$ , $V_{GS} = 0\text{V}$		120	ns
$Q_{RM}$			0.53	$\mu\text{C}$
$I_{RM}$			- 8.9	A

Note 1: Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

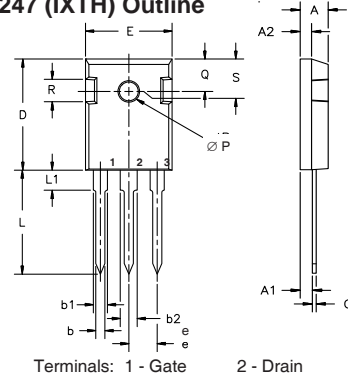
IXYS reserves the right to change limits, test conditions, and dimensions.

### TO-263 (IXTA) Outline



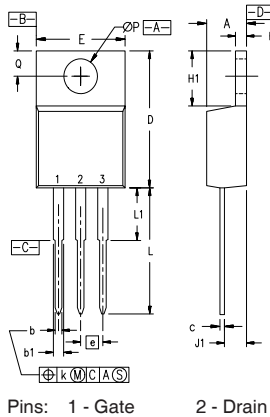
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

### TO-247 (IXTH) Outline



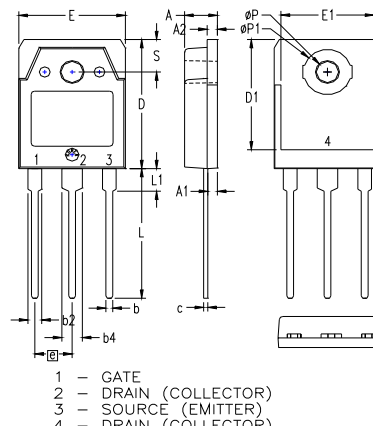
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216

### TO-220 (IXTP) Outline



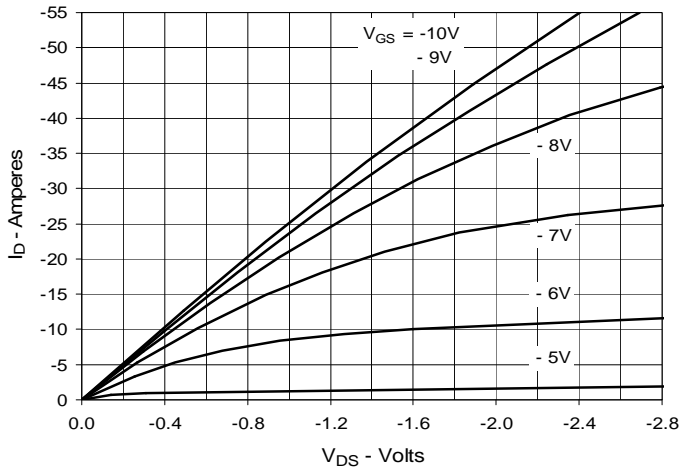
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
∅P	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

### TO-3P (IXTQ) Outline

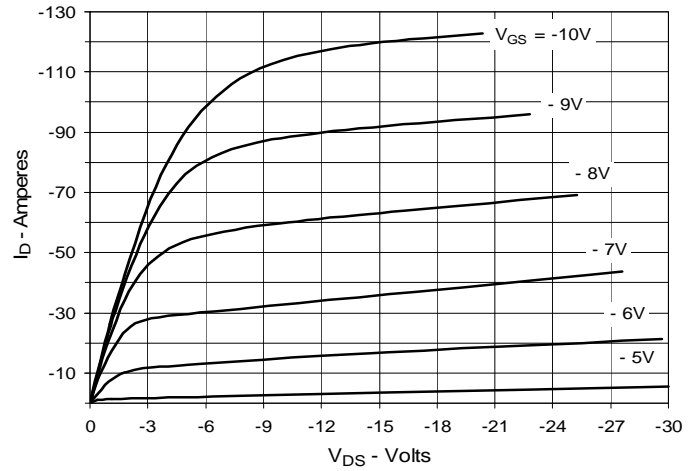


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.799	19.80	20.30
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
∅P	.126	.134	3.20	3.40
∅P1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

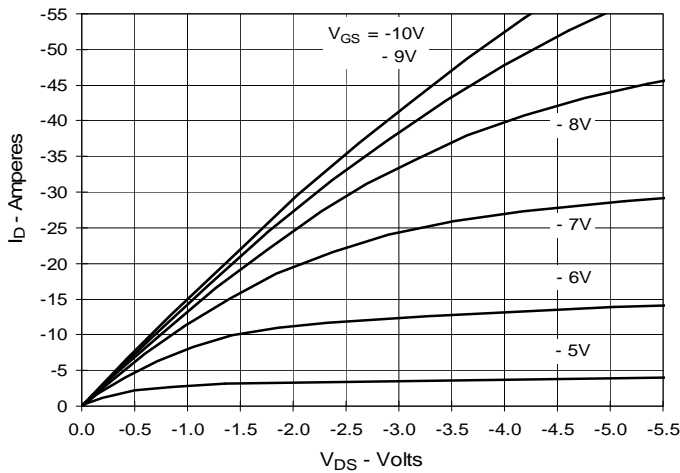
**Fig. 1. Output Characteristics @ 25°C**



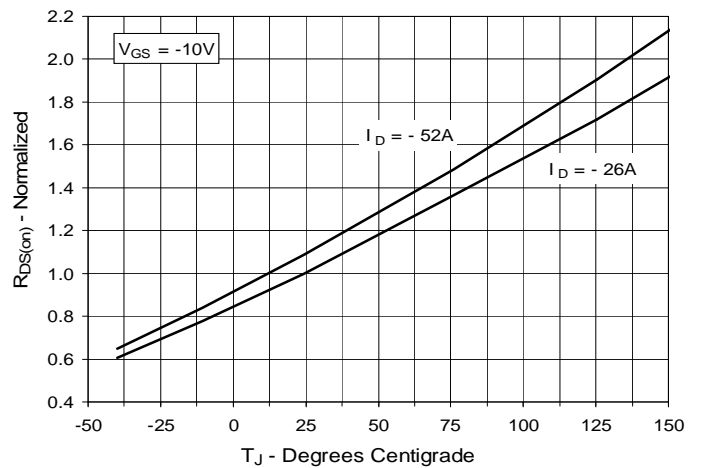
**Fig. 2. Extended Output Characteristics @ 25°C**



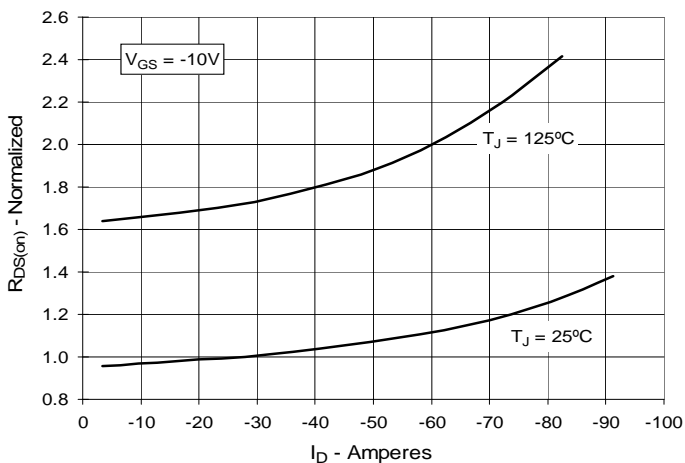
**Fig. 3. Output Characteristics @ 125°C**



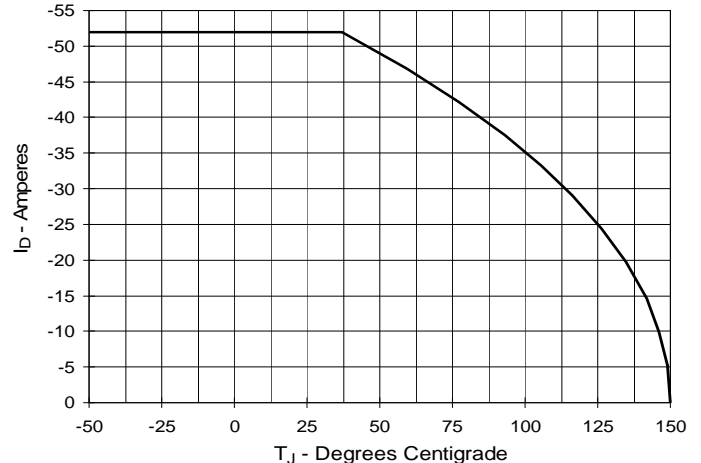
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = -26A$  vs. Junction Temperature**



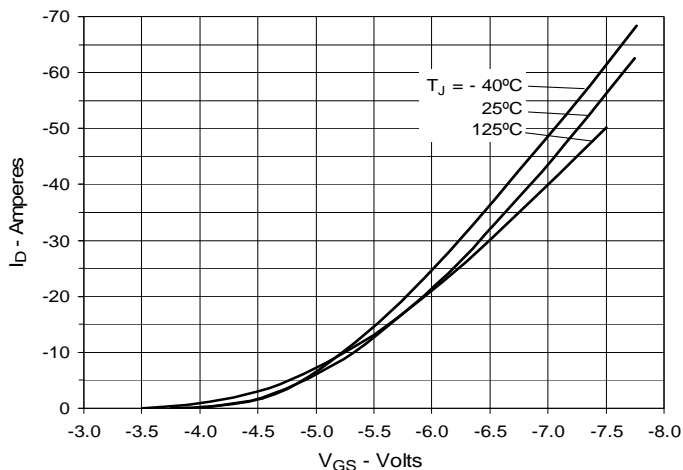
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = -26A$  vs. Drain Current**



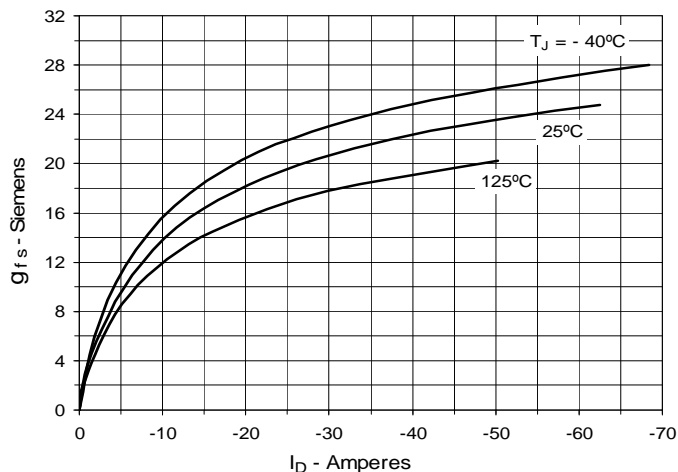
**Fig. 6. Maximum Drain Current vs. Case Temperature**



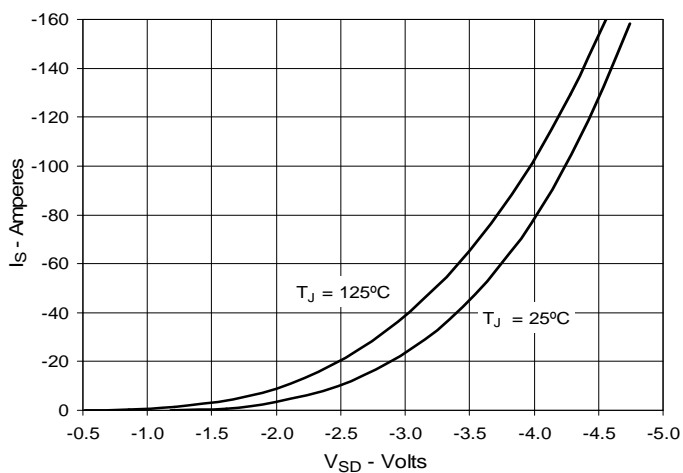
**Fig. 7. Input Admittance**



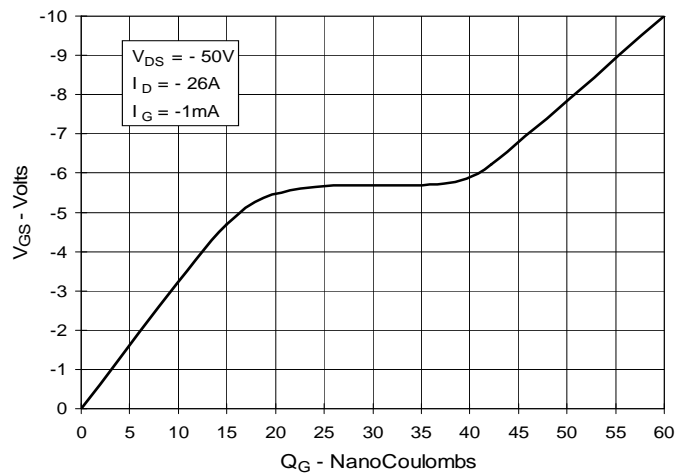
**Fig. 8. Transconductance**



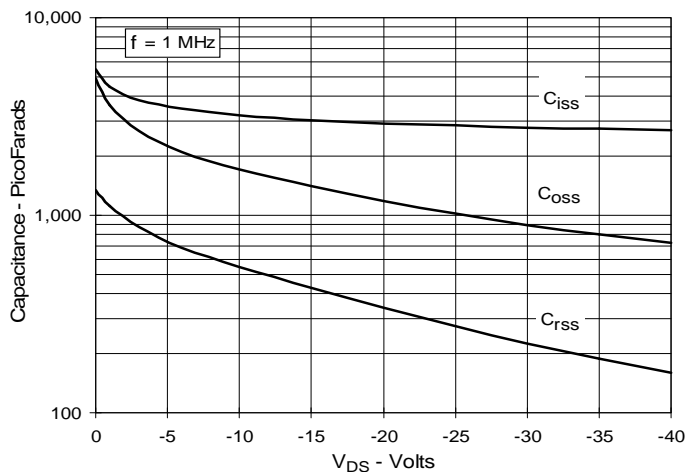
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**

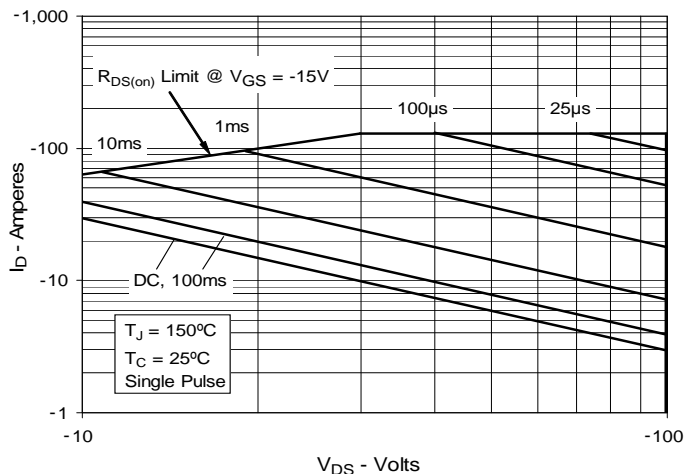
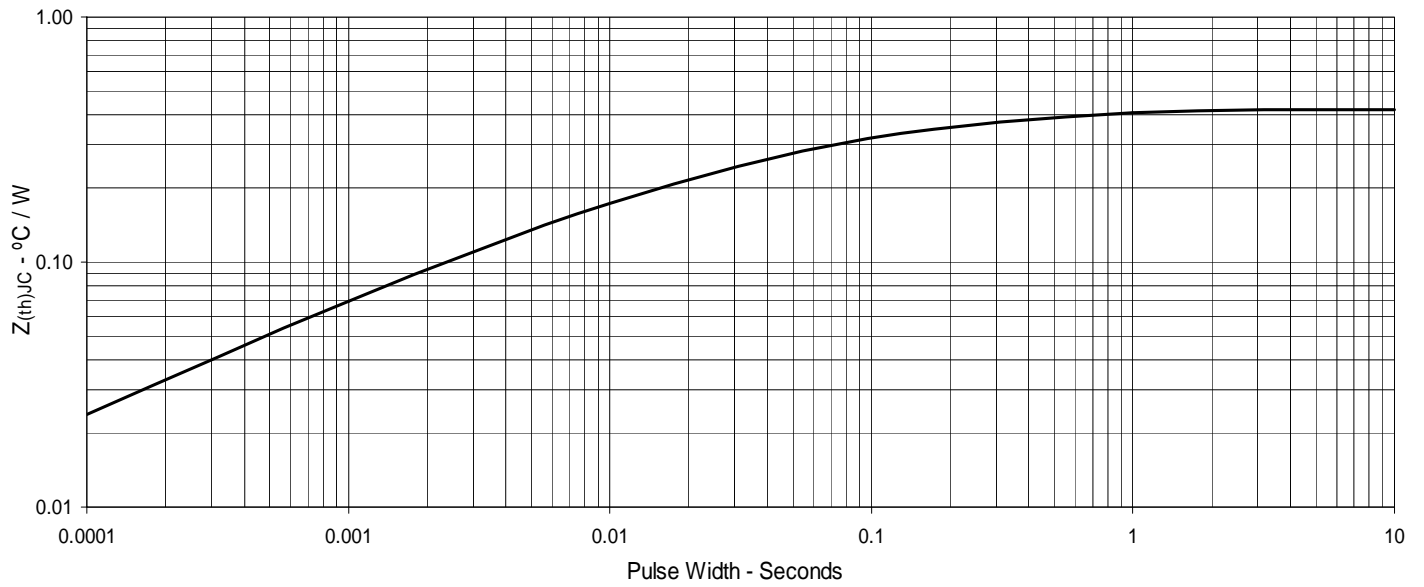


Fig. 13. Maximum Transient Thermal Impedance



## Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

 [View IXTH52P10P on WIN SOURCE](#)

 [IXYS Information](#)

## Optimize Your Supply Chain with WIN SOURCE Solutions

-  Global Sourcing Solution
-  Obsolete Management
-  Cost Control Management
-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management